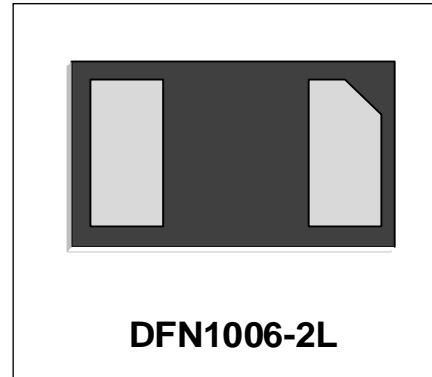




## Features

- 36 Watts Peak Pulse Power per Line ( $t_p = 8/20\mu s$ )
- Protects one I/O or power line
- Low Clamping Voltage
- Working Voltage: 5 V
- Low Leakage Current
- AEC-Q101 Qualified



## IEC Compatibility (EN61000-4)

- IEC 61000-4-2 (ESD)  $\pm 30kV$  (air),  $\pm 30kV$  (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 3A (8/20 $\mu s$ )

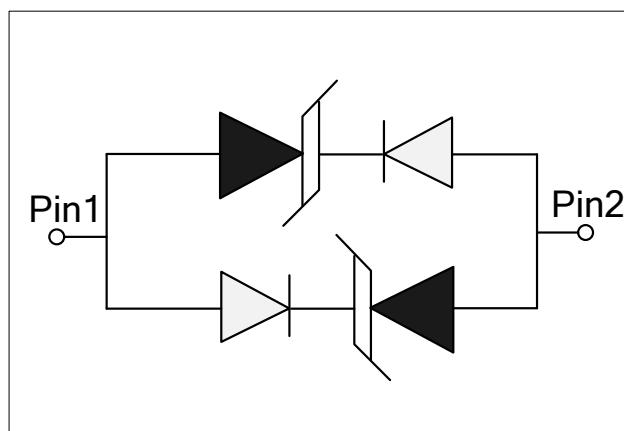
## Mechanical Characteristics

- DFN1006-2L package
- Marking : Marking Code
- Packaging : Tape and Reel per EIA 481
- RoHS Compliant

## Applications

- Laptop Computers
- Cellular Phones
- Digital Cameras
- Personal Digital Assistants (PDAs)

## Schematic & PIN Configuration



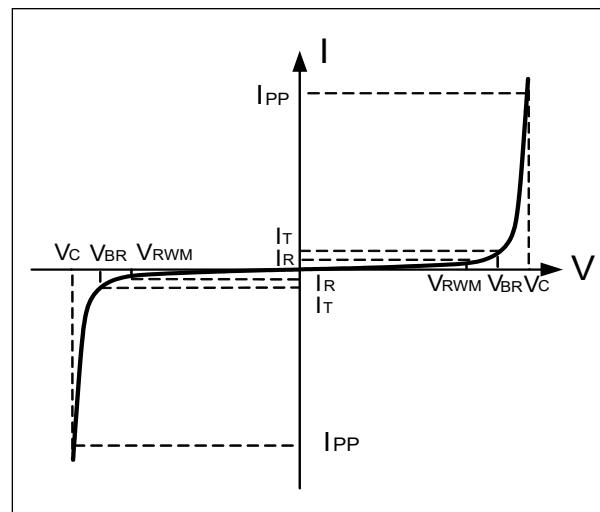


## Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	$P_{PP}$	36	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ )	$I_{PP}$	3	A
Operating Temperature	$T_J$	-55 to +125	°C
Storage Temperature	$T_{STG}$	-55 to +150	°C

## Electrical Parameters (T=25°C)

Symbol	Parameter
$I_{PP}$	Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Reverse Stand-Off Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$I_T$	Test Current
$V_{BR}$	Reverse Breakdown Voltage @ $I_T$



## Electrical Characteristics

DW05DUCF-BF-AT-E						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T = 1\text{mA}$	6		9	V
nReverse Leakage Current	$I_R$	$V_{RWM} = 5\text{V}, T = 25^\circ\text{C}$			500	nA
Clamping Voltage	$V_C$	$I_{PP} = 3\text{A}, t_p = 8/20\mu\text{s}$		10.5	12	V
Dynamic Resistance <sup>1,2</sup>	$R_{DYN}$	TLP=0.2/100ns		0.6		Ω
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP} = 4\text{A}, t_p = 0.2/100\text{ns} (\text{TLP})$		9.8		V
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP} = 16\text{A}, t_p = 0.2/100\text{ns} (\text{TLP})$		17.5		V
Junction Capacitance	$C_J$	$V_R = 0\text{V}, f = 1\text{MHz}$		0.4	0.6	pF

Notes : 1、TLP Setting :  $t_p=100\text{ns}$ ,  $t_i=0.2\text{ns}$ ,  $I_{TLP}$  and  $V_{TLP}$  sample window: $t_1=70\text{ns}$  to  $t_2=90\text{ns}$ .

2、Dynamic resistance calculated from  $I_{PP}=4\text{A}$  to  $I_{PP}=16\text{A}$  using "Best Fit".

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## Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

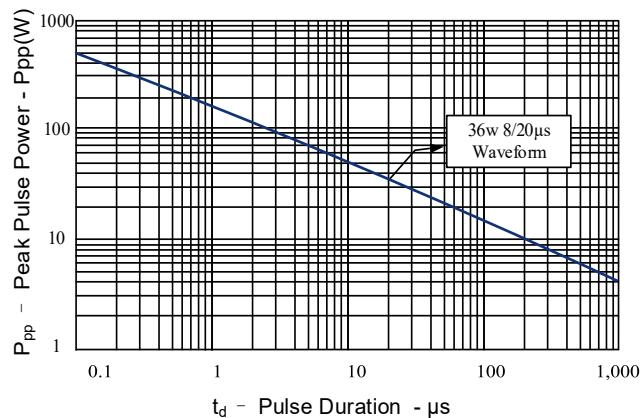


Figure 2: Power Derating Curve

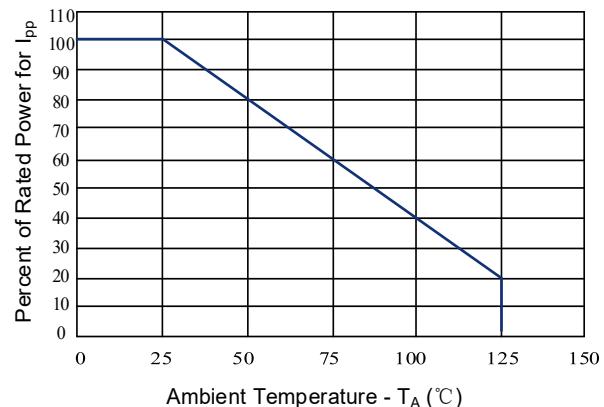


Figure 3: Clamping Voltage vs. Peak Pulse Current

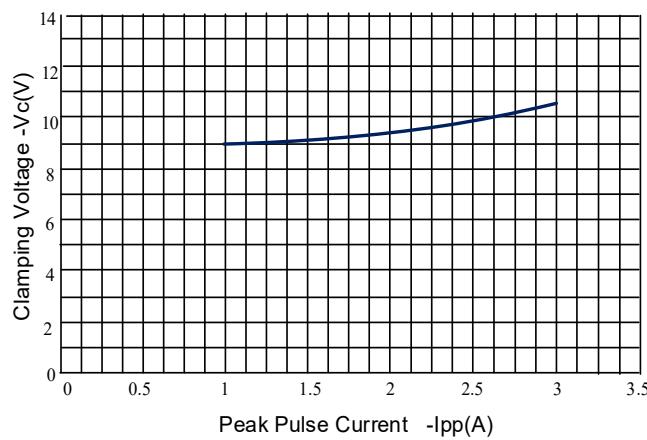


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

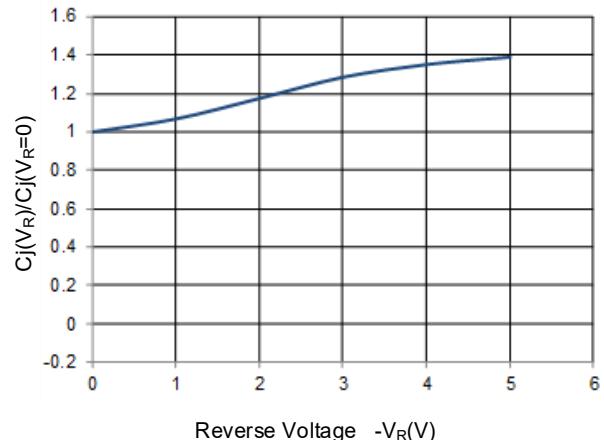


Figure 5: TLP Positive I-V Curve

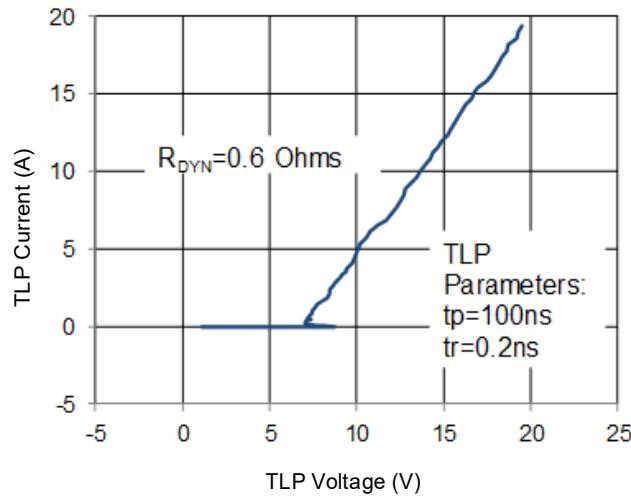
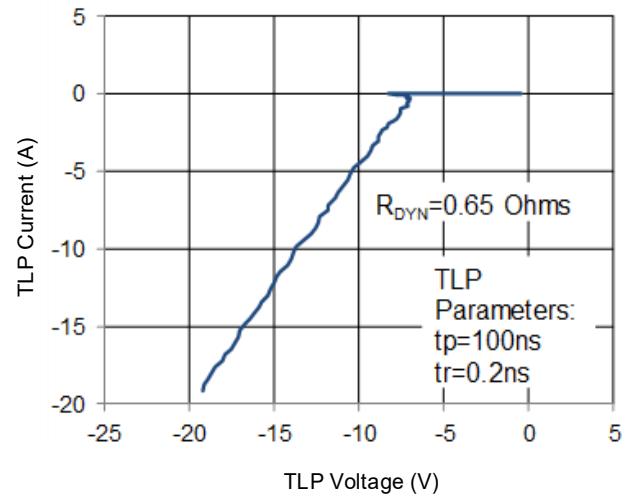


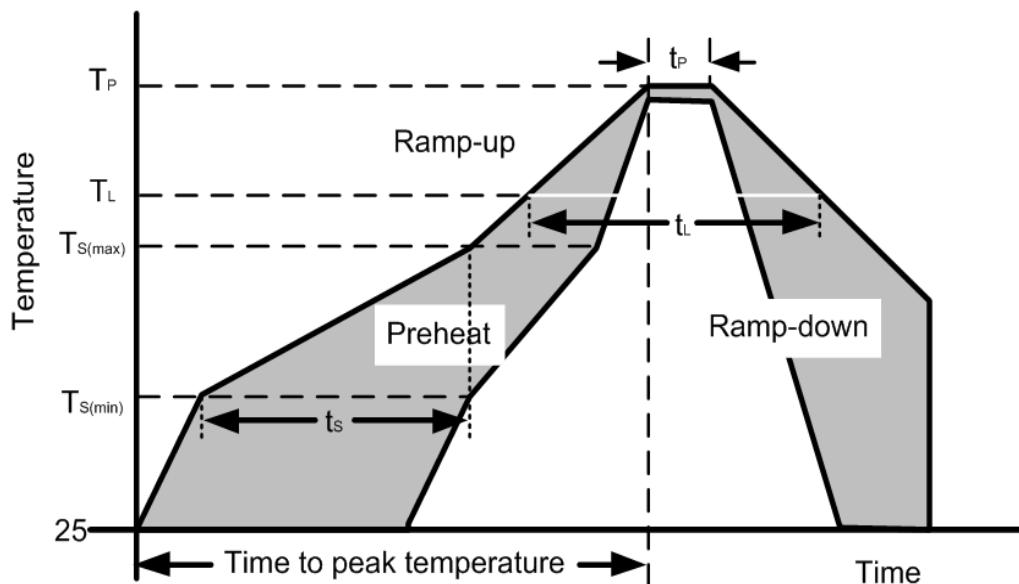
Figure 6: TLP Negative I-V Curve





## Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	Temperature Min ( $T_{s(\min)}$ )	150°C
	Temperature Max ( $T_{s(\max)}$ )	200°C
	Time (min to max) ( $t_s$ )	60 – 190 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{s(\max)}$ to $T_L$ —Ramp-up Rate		5°C/second max
Reflow	Temperature ( $T_L$ ) (Liquidus)	217°C
	Temperature ( $t_L$ )	60 – 150 seconds
	Peak Temperature ( $T_P$ )	260+0/-5 °C
Time within actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_P$ )		8 minutes Max.
Do not exceed		280°C

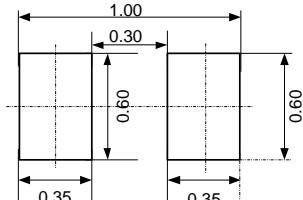




## Outline Drawing –DFN1006-2L

PACKAGE OUTLINE			
SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.45	0.50	0.55
A1	0	0.02	0.05
b	0.45	0.50	0.55
C	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05REF		
h	0.07	0.12	0.17

## Land Pattern



## Marking Codes

Part Number	Marking Code
DW05DUCF-BF-AT-E	5 T

## Package Information

Qty: 10k/Reel